TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

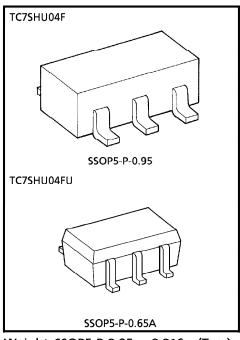
TC7SHU04F, TC7SHU04FU

INVERTER

The TC7SHU04 is an advanced high speed CMOS INVERTER fabricated with silicon gate C²MOS technology. It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation. Since the internal circuit is composed of a single stage inverter, it can be used in analog applications such as crystal oscillators. An input protection circuit ensures that 0 to 7V can be applied to the input pins without regard to the supply voltage. This device can be used to interfase 5V to 3V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

FEATURES

- High Speed \cdots $t_{pd} = 3.5$ ns (Typ.) at $V_{CC} = 5V$
- Low Power Dissipation $I_{CC} = 2\mu A$ (Max.) at
- High Noise Immunity ··············· V_{NIH} = V_{NIL}
 = 10% V_{CC} (Min.)
- Power Down Protection is provided on all inputs.
- Balanced Propagation Delays ······ t_{pLH}≒t_{pHL}
- Wide Operating Voltage Range····· V_{CC} (opr) = 2~5.5V

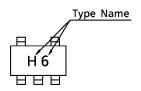


Weight SSOP5-P-0.95 : 0.016g (Typ.) SSOP5-P-0.65A : 0.006g (Typ.)

MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	Vcc	-0.5~7.0	V
DC Input Voltage	VIN	-0.5~7.0	٧
DC Output Voltage	Vout	-0.5~V _{CC} +0.5	V
Input Diode Current	ΙΚ	- 20	mA
Output Diode Current	loк	± 20	mA
DC Output Current	IOUT	± 25	mA
DC V _{CC} /Ground Current	Icc	± 50	mA
Power Dissipation	PD	200	mW
Storage Temperature	T _{stg}	-65∼150	°C
Lead Temperature (10s)	TL	260	°C

MARKING



TRUTH TABLE

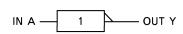
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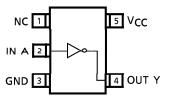
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LOGIC DIAGRAM

PIN ASSIGNMENT (TOP VIEW)





RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	Vcc	2.0~5.5	V
Input Voltage	VIN	0~5.5	V
Output Voltage	Vout	0~V _{CC}	V
Operating Temperature	T _{opr}	- 40~85	°C

DC ELECTRICAL CHARACTERISTICS

PARAMETER SYMBOL CIR-CUIT TEST CONDITION		ONDITION		Ta = 25°C			Ta = − 40~85°C		LINUT		
			I EST C	Vcc	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT	
High-Level Input					2.0	1.7	_	_	1.7	_	
Voltage	VIH	_		_		Vcc	_		Vcc	_	V
					5.5	×0.8			×0.8		
Low-Level Input					2.0		_	0.30	<u> </u>	0.30	
Voltage	V _{IL}	–	-		3.0~			Vcc	<u> </u>	VCC	V
					5.5			×0.2		×0.2	
	Voн	_		I _{OH} = -50μA	2.0	1.8	2.0	—	1.8	—	_
High Level			VIN = VIL		3.0	2.7	3.0	 	2.7	_	
Output-Voltage			-		4.5	4.0	4.5	_	4.0	_	
Output-voltage			V _{IN} = GND	$I_{OH} = -4mA$	3.0	2.58	_	—	2.48	_	
				$I_{OH} = -8mA$	4.5	3.94	_	—	3.80	—	
				I _{OL} = 50μΑ	2.0	_	0.0	0.2	_	0.2	
Low-Level Output-Voltage			V _{IN} = V _{IH}		3.0	—	0.0	0.3	l —	0.3	
	VOL				4.5	_	0.0	0.5	_	0.5	V
			V _{IN} = V _{CC}	I _{OL} = 4mA	3.0	_	_	0.36	_	0.44	
				IOL = 8mA	4.5	_	_	0.36	_	0.44	
Input Leakage Current	IN	_	V _{IN} = 5.5V or GND		0~ 5.5	_	_	± 0.1	_	± 1.0	
Quiescent Supply Current	^l cc	_	V _{IN} = V _{CC} or GND		5.5	_	_	2.0		20.0	μ A

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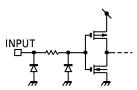
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AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3ns$)

PARAMETER SYMBOL	TEST	TEST CONDITION			Ta = 25°C			Ta = − 40~85°C		UNIT	
	CIR- CUIT		V _{CC} (V)	C _L (pF)	MIN.	TYP.	MAX.	MIN.	MAX.		
Propagation tpLH Delay Time tpHL		_	_	3.3 ± 0.3	15	_	5.0	8.9	1.0	10.5	ns
					50	_	7.5	11.4	1.0	13.0	
				5.0 ± 0.5	15	_	3.5	5.5	1.0	6.5	
					50	1	5.0	7.0	1.0	8.0	
Input Capacitance	C _{IN}	_	_			I	5	10		10	
Power Dissipation Capacitance	C _{PD}		Note (1)			_	6			_	pF

Note (1): C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation : $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

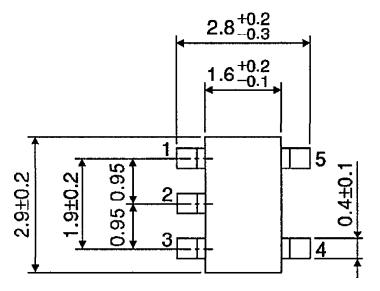
INPUT EQUIVALENT CIRCUIT

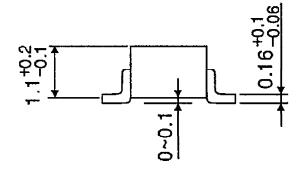


OUTLINE DRAWING

SSOP5-P-0.95

Unit: mm



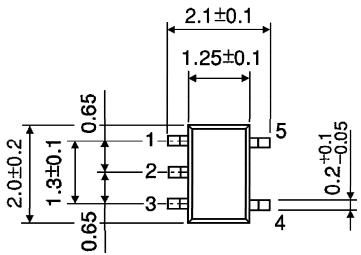


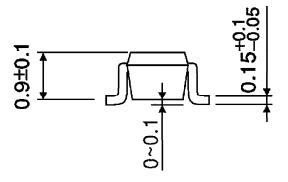
Weight: 0.016g (Typ.)

Unit: mm

OUTLINE DRAWING

SSOP5-P-0.65A





Weight: 0.006g (Typ.)